

2SA1262

Silicon PNP Epitaxial Planar Transistor (Complement to type 2SC3179)

Application : Audio and General Purpose

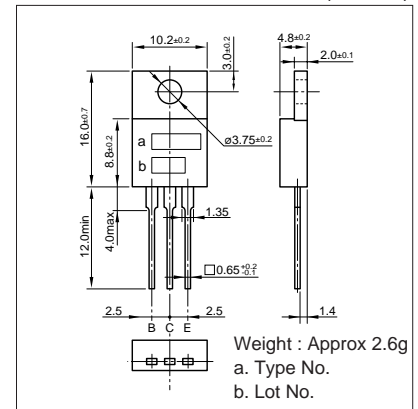
Absolute maximum ratings (Ta=25°C)

Symbol	2SA1262	Unit
V _{CB0}	-60	V
V _{CE0}	-60	V
V _{EB0}	-6	V
I _c	-4	A
I _B	-1	A
P _c	30(T _c =25°C)	W
T _j	150	°C
T _{stg}	-55 to +150	°C

Electrical Characteristics (Ta=25°C)

Symbol	Conditions	2SA1262	Unit
I _{CB0}	V _{CB} =-60V	-100max	μA
I _{EB0}	V _{EB} =-6V	-100max	μA
V(BR) _{CEO}	I _c =-25mA	-60min	V
h _{FE}	V _{CE} =-4V, I _c =-1A	40min	
V _{CE(sat)}	I _c =-2A, I _B =-0.2A	-0.6max	V
f _r	V _{CE} =-12V, I _E =0.2A	15typ	MHZ
C _{oB}	V _{CB} =-10V, f=1MHz	90typ	pF

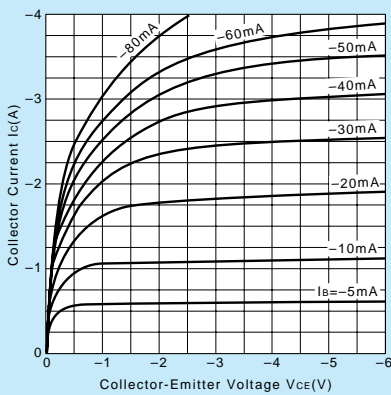
External Dimensions MT-25(TO220)



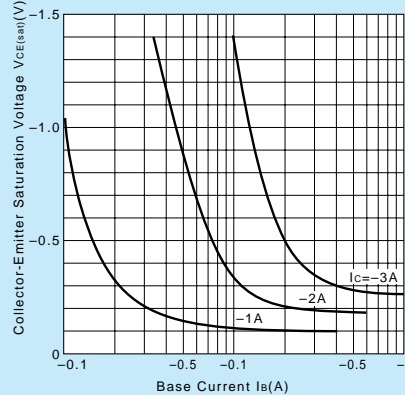
Typical Switching Characteristics (Common Emitter)

V _{CC} (V)	R _L (Ω)	I _c (A)	V _{BB1} (V)	V _{BB2} (V)	I _{B1} (mA)	I _{B2} (mA)	t _{on} (μs)	t _{stg} (μs)	t _f (μs)
-20	10	-2	-10	5	-200	200	0.25typ	0.75typ	0.25typ

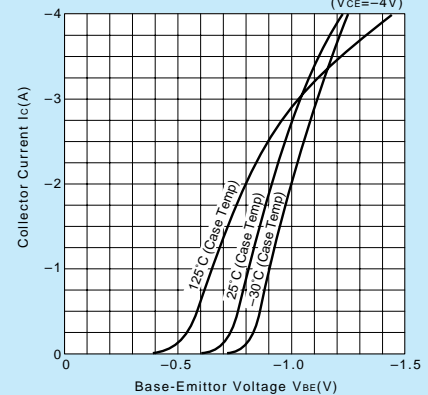
I_c-V_{CE} Characteristics (Typical)



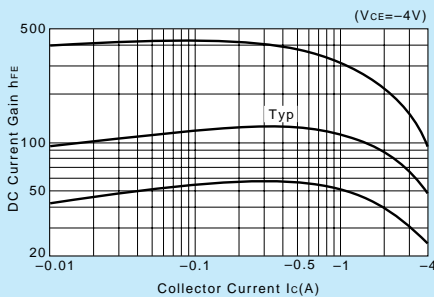
V_{CE(sat)}-I_B Characteristics (Typical)



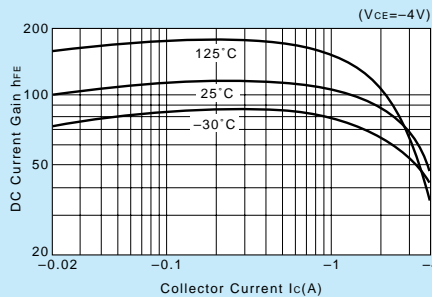
I_c-V_{BE} Temperature Characteristics (Typical)



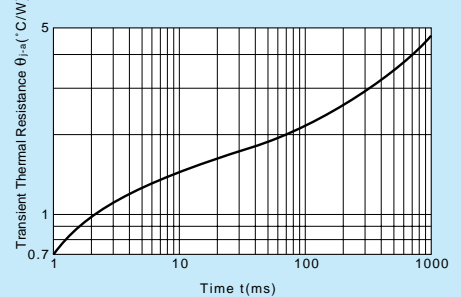
h_{FE}-I_c Characteristics (Typical)



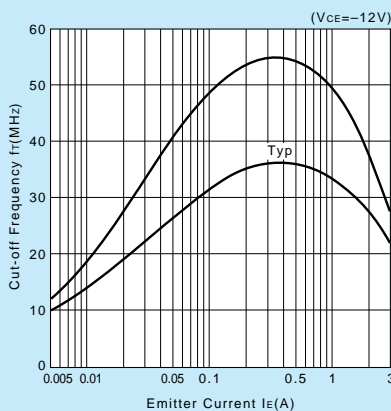
h_{FE}-I_c Temperature Characteristics (Typical)



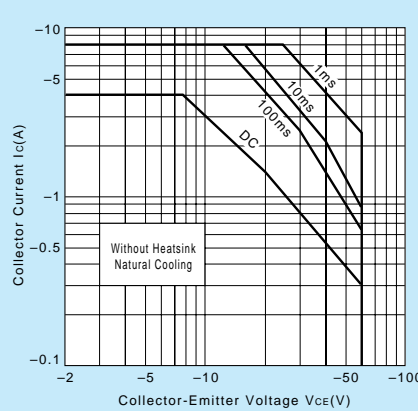
θ_{j-a}-t Characteristics



f_T-I_E Characteristics (Typical)



Safe Operating Area (Single Pulse)



P_c-T_a Derating

